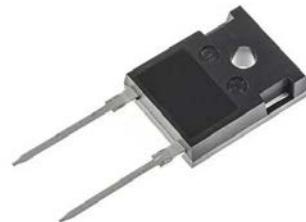




## Features

- 1.2kV Schottky Rectifier
- Zero Reverse Recovery Current
- High-Frequency Operation
- Temperature-Independent Switching
- Extremely Fast Switching
- Positive Temperature Coefficient on  $V_F$
- Increased Creepage/Clearance Distance



TO247-2L  
Package

## Benefits

- Replace Bipolar with Unipolar Rectifiers
- Essentially No Switching Losses
- Higher Efficiency
- Reduction of Heat Sink Requirements
- Parallel Devices Without Thermal Runaway



## Applications

- Switch Mode Power Supplies (SMPS)
- Boost diodes in PFC or DC/DC stages
- Free Wheeling Diodes in Inverter stages
- AC/DC converters



Part Number	Package	Qty(PCS)
HIDWD20G120C5XKSA1	TO247-2L	30

## Maximum Ratings ( $T_C=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions	Note
$V_{RRM}$	Repetitive Peak Reverse Voltage	1200	V		
$V_{RSM}$	Surge Peak Reverse Voltage	1300	V		
$V_R$	DC Peak Reverse Voltage	1200	V		
$I_F$	Continuous Forward Current	54 26 20	A	$T_c=25^\circ\text{C}$ $T_c=135^\circ\text{C}$ $T_c=156^\circ\text{C}$	Fig. 3
$I_{FRM}$	Repetitive Peak Forward Surge Current	86 56	A	$T_c=25^\circ\text{C}$ , $t_p=10$ ms, Half Sine Pulse $T_c=110^\circ\text{C}$ , $t_p=10$ ms, Half Sine Pulse	
$I_{FSM}$	Non-Repetitive Forward Surge Current	130 104	A	$T_c=25^\circ\text{C}$ , $t_p=10$ ms, Half Sine Pulse $T_c=110^\circ\text{C}$ , $t_p=10$ ms, Half Sine Pulse	Fig. 8
$I_{F,Max}$	Non-Repetitive Peak Forward Current	1150 950	A	$T_c=25^\circ\text{C}$ , $t_p=10$ ms, Pulse $T_c=110^\circ\text{C}$ , $t_p=10$ ms, Pulse	Fig. 8
$P_{tot}$	Power Dissipation	246 106.5	W	$T_c=25^\circ\text{C}$ $T_c=110^\circ\text{C}$	Fig. 4
$dV/dt$	Diode $dV/dt$ ruggedness	200	V/ns	$V_R=0-960$ V	
$\int i^2 dt$	$i^2 t$ value	84.5 54	A <sup>2</sup> s	$T_c=25^\circ\text{C}$ , $t_p=10$ ms $T_c=110^\circ\text{C}$ , $t_p=10$ ms	
$T_J$ , $T_{stg}$	Operating Junction and Storage Temperature	-55 to +175	°C		
	TO-247 Mounting Torque	1 8.8	Nm lbf-in	M3 Screw 6-32 Screw	



## Electrical Characteristics

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
$V_F$	Forward Voltage	1.5 2.2	1.8 3	V	$I_F = 20 \text{ A}$ $T_J = 25^\circ\text{C}$ $I_F = 20 \text{ A}$ $T_J = 175^\circ\text{C}$	Fig. 1
$I_R$	Reverse Current	35 65	200 400	$\mu\text{A}$	$V_R = 1200 \text{ V}$ $T_J = 25^\circ\text{C}$ $V_R = 1200 \text{ V}$ $T_J = 175^\circ\text{C}$	Fig. 2
$Q_C$	Total Capacitive Charge	99		nC	$V_R = 800 \text{ V}$ , $I_F = 20 \text{ A}$ $dI/dt = 200 \text{ A}/\mu\text{s}$ $T_J = 25^\circ\text{C}$	Fig. 5
C	Total Capacitance	1500 93 67		pF	$V_R = 0 \text{ V}$ , $T_J = 25^\circ\text{C}$ , $f = 1 \text{ MHz}$ $V_R = 400 \text{ V}$ , $T_J = 25^\circ\text{C}$ , $f = 1 \text{ MHz}$ $V_R = 800 \text{ V}$ , $T_J = 25^\circ\text{C}$ , $f = 1 \text{ MHz}$	Fig. 6
$E_C$	Capacitance Stored Energy	28		$\mu\text{J}$	$V_R = 800 \text{ V}$	Fig. 7

Note: This is a majority carrier diode, so there is no reverse recovery charge.

## Thermal Characteristics

Symbol	Parameter	Typ.	Unit	Note
$R_{\theta JC}$	Thermal Resistance from Junction to Case	0.61	°C/W	Fig. 9

## Typical Performance

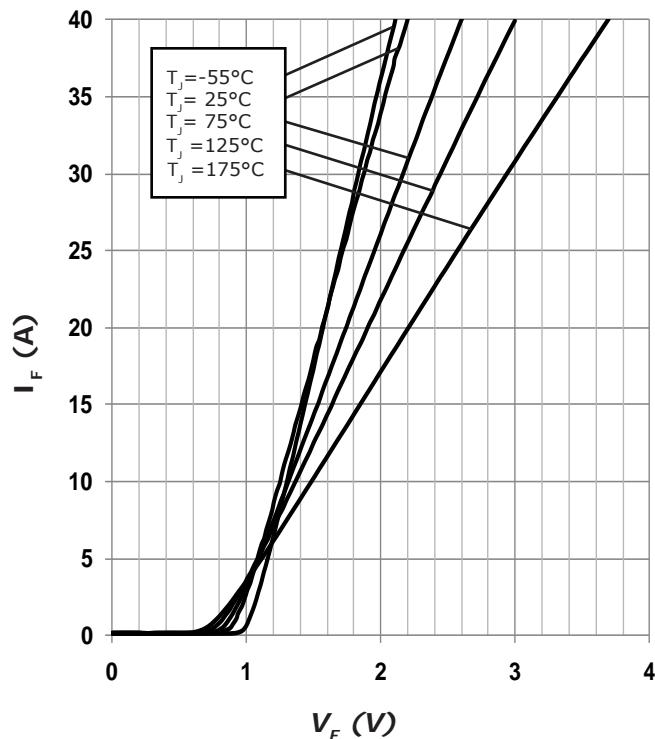


Figure 1. Forward Characteristics

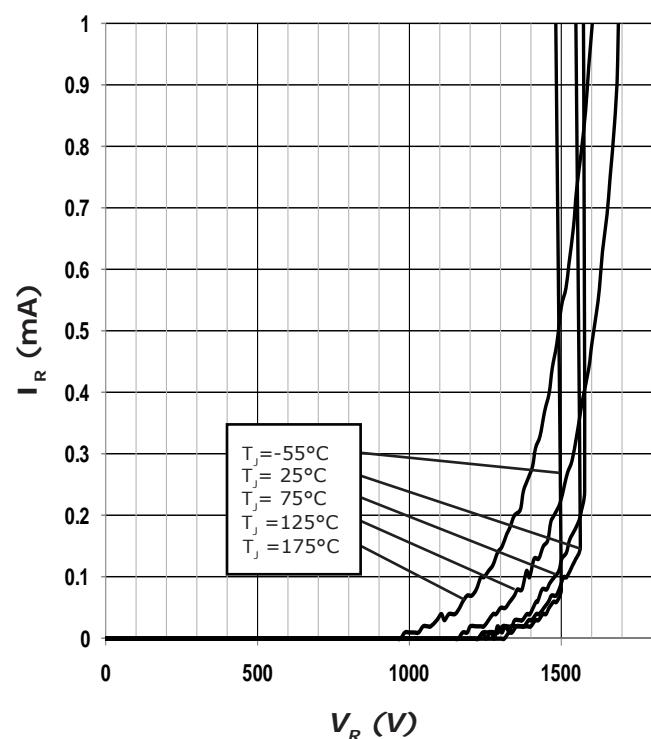


Figure 2. Reverse Characteristics



## Typical Performance

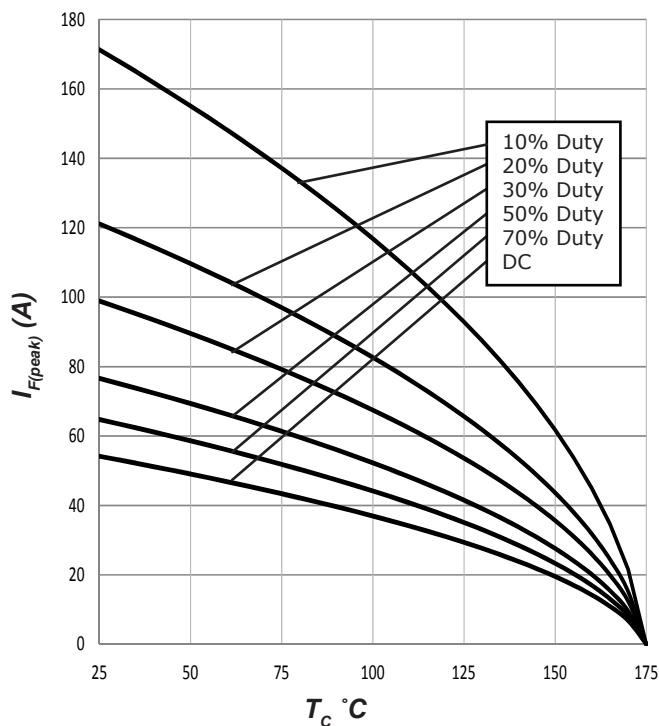


Figure 3. Current Derating

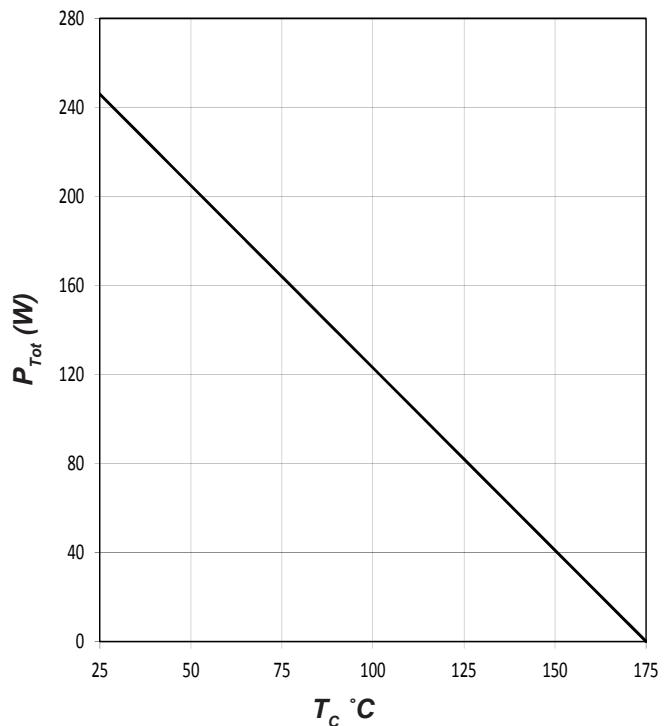


Figure 4. Power Derating

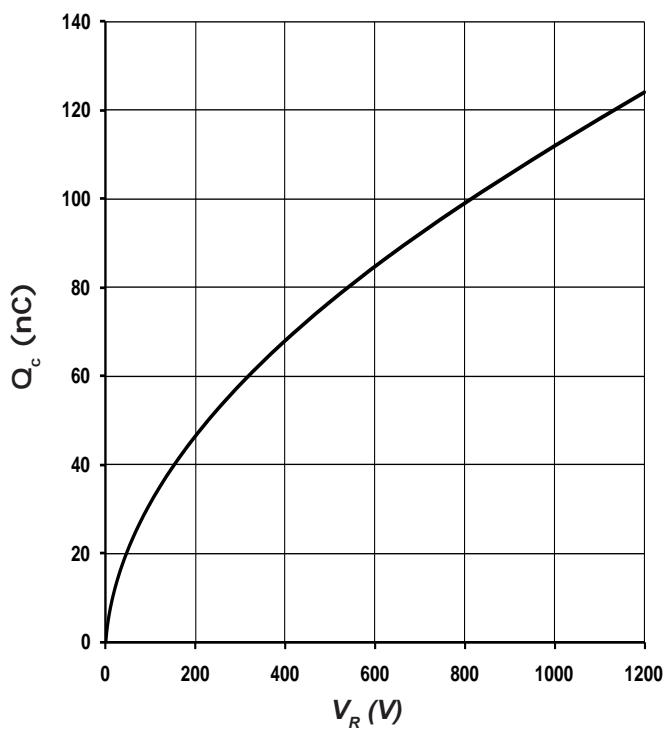


Figure 5. Recovery Charge vs. Reverse Voltage

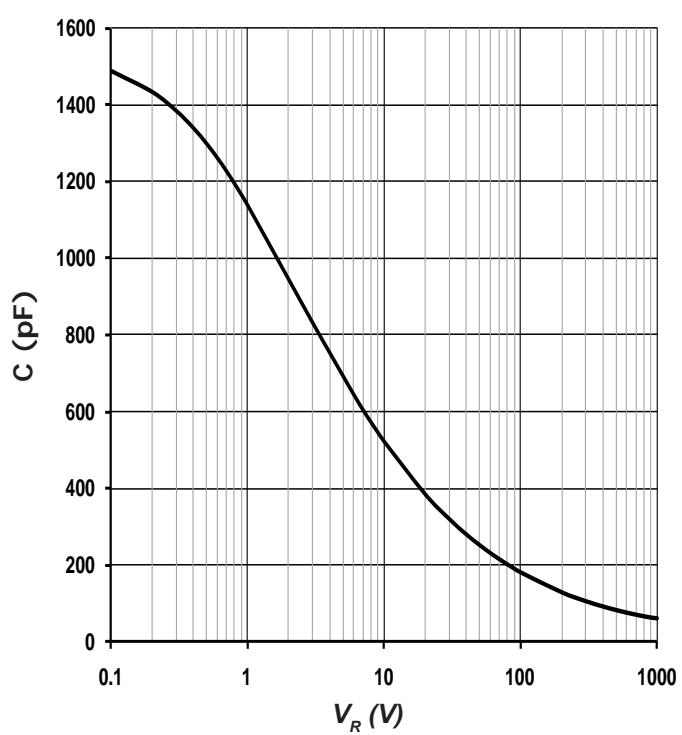


Figure 6. Capacitance vs. Reverse Voltage



## Typical Performance

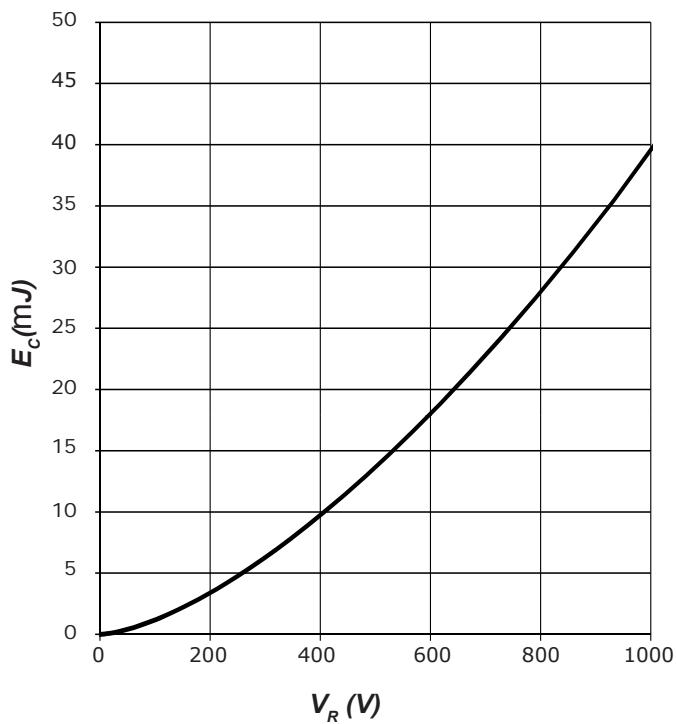


Figure 7. Typical Capacitance Stored Energy

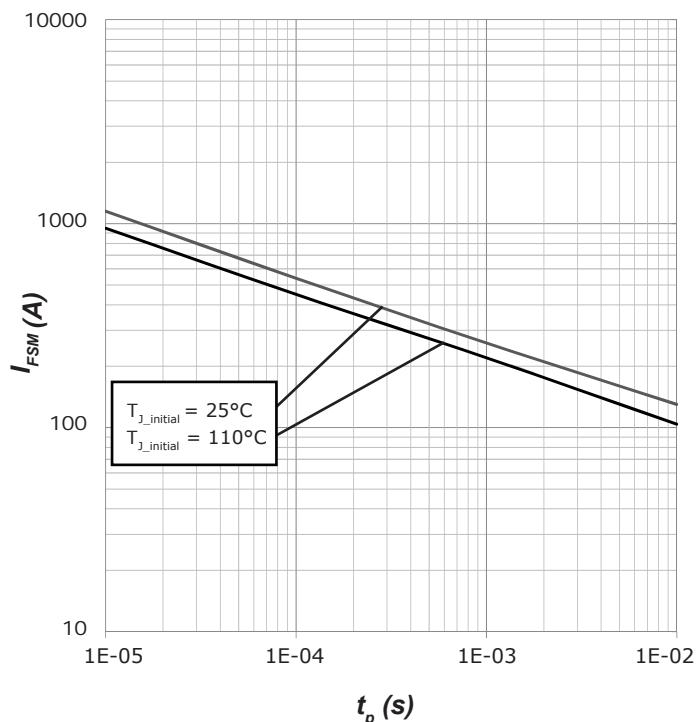


Figure 8. Non-Repetitive Peak Forward Surge Current versus Pulse Duration (sinusoidal waveform)

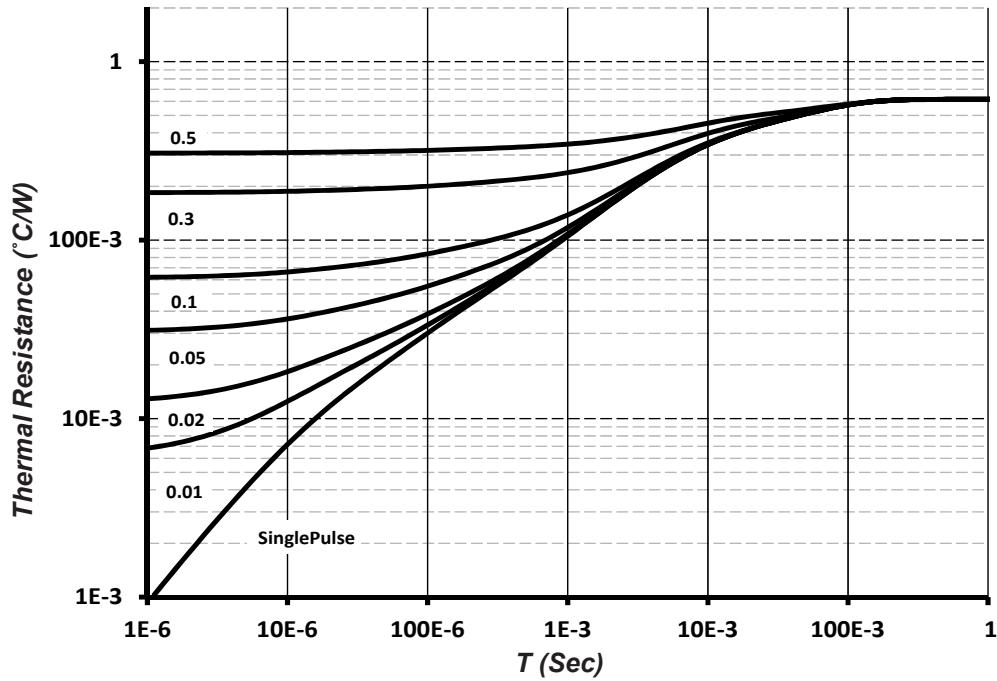
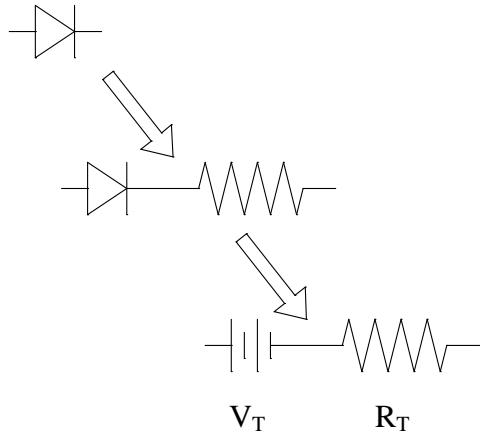


Figure 9. Transient Thermal Impedance



## Diode Model



$$V_{fT} = V_T + I_f \cdot R_T$$

$$V_T = 0.97 + (T_J^* - 1.40 \cdot 10^{-3})$$
$$R_T = 0.023 + (T_J^* \cdot 2.71 \cdot 10^{-4})$$

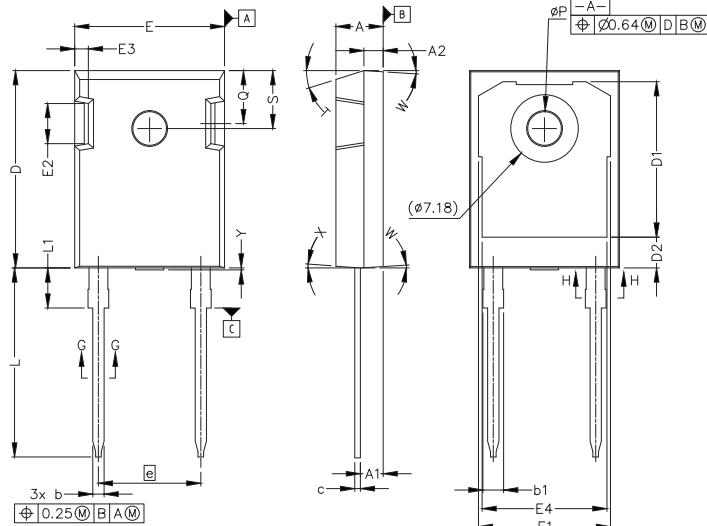
Note:  $T_J$  = Diode Junction Temperature in Degrees Celsius,  
valid from 25°C to 175°C



## Package Dimensions

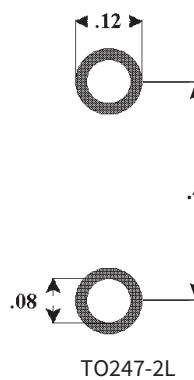
Package: TO247-2L

All dimensions in mm.



SYM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.83	5.21	.190	.205
A1	2.29	2.54	.090	.100
A2	1.91	2.16	.075	.085
b'	1.07	1.28	.042	.050
b	1.07	1.33	.042	.052
b1	1.91	2.41	.075	.095
b2	1.91	2.16	.075	.085
c'	0.55	0.65	.022	.026
c	0.55	0.68	.022	.027
D	20.80	21.10	.819	.831
D1	16.25	17.35	.640	.683
D2	2.86	3.16	.112	.124
E	15.75	16.13	.620	.635
E1	13.10	14.15	.516	.557
E2	3.68	5.10	.145	.201
E3	1.00	1.90	.039	.075
E4	12.38	13.43	.487	.529
e	10.88	BSC	.428	BSC
L	19.81	20.32	.780	.800
L1	4.10	4.40	.161	.173
$\phi P$	3.51	3.65	.138	.144
Q	5.49	6.00	.216	.236
S	6.04	6.30	.238	.248
T	17.5° REF.			
W	3.5° REF.			
X	4° REF.			
Y	0	0.50	0	0.020

## Recommended Solder Pad Layout



TO247-2L

*all units are in inches*



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